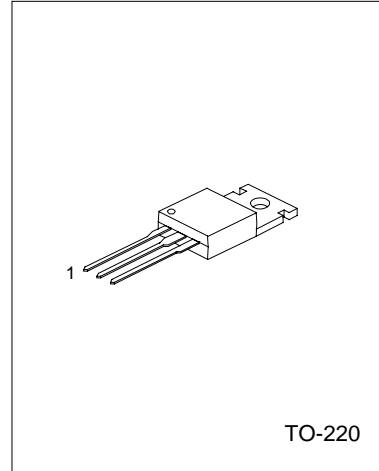


UTC MJE3055T NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

The UTC MJE3055T is designed for general purpose of amplifier and switching applications.



TO-220

1:BASE 2: COLLECTOR 3: EMITTER

ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	70	V
Collector-emitter voltage	V _{CEO}	60	V
Emitter-base voltage	V _{EBO}	5	V
Total Power Dissipation(T _a =25°C)	P _c	75	W
Collector current	I _c	10	A
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C
Base Current	I _B	6	A

ELECTRICAL CHARACTERISTICS(T_a=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	V _{CEO}	I _c =200mA	60			V
Collector-Base Breakdown Voltage	V _{CB0}	I _c =10mA	70			V
Emitter-Base Breakdown Voltage	V _{EBO}	I _E =10mA	5			V
Collector cut-off current	I _{CB0}	V _{CB} =70V			1	mA
	I _{CEO}	V _{CE} =30V			700	μA
	I _{CEx}	V _{CE} =70V, V _{EB(off)} =1.5V			1	mA
Emitter cut-off current	I _{EBO}	V _{EB} =5V			5	mA
Collector-emitter saturation voltage	V _{CE(SAT)1}	I _c =4A, I _B =0.4A			1.1	V
	V _{CE(SAT)2}	I _c =10A, I _B =3.3A			8	V
Base-emitter on voltage	V _{BE(ON)}	V _{CE} =4V, I _c =4A			1.8	V
DC current gain	h _{FE1}	I _c =4A, V _{CE} =4V	20		100	
	h _{FE2}	I _c =4A, V _{CE} =10V	5			
Current gain bandwidth product	f _T	V _{CE} =10V, I _c =0.5A, f=1MHz	2			MHZ